

Page 49, delete the whole paragraph starting in line 14 and replace it with the following new paragraph:

912 It should be noted that the foregoing description is not limited to the (111) surface of the Si crystal but is valid also with a crystal surface near the (111) surface with an offset angle in an arbitrary direction from the (111) surface.

See the attached Appendix for the changes made to effect the above paragraph

IN THE CLAIMS:

Please enter the following amended claims:

913 4. (Amended) A semiconductor device as claimed in claim 1, wherein said Si oxide film contains Kr with a surface density of $5 \times 10^{11} \text{cm}^{-2}$ or less at a surface thereof.

10. (Amended) A semiconductor device as claimed in claim 9, wherein said Si nitride film contains Ar or Kr with a surface density of $5 \times 10^{11} \text{cm}^{-2}$ or less.

11. (Amended) A semiconductor device as claimed in claim 9, wherein said Si nitride film contains hydrogen atoms therein.

914 12. (Amended) A semiconductor device as claimed in claim 9, further comprising a gate electrode on said Si nitride film.

27. (Amended) A ferroelectric memory device, comprising:

a Si substrate;

a gate insulation film formed on said Si substrate;

a gate electrode of polysilicon formed on said gate insulation film;

915 a Si nitride film formed on said gate insulation film; and

a ferroelectric film formed on said Si nitride film; and

another electrode formed on said ferroelectric film, said Si nitride film containing Ar or Kr.

34. (Amended) A method of forming a Si nitride film as claimed in claim 33, wherein said nitriding step is conducted at a temperature of 550°C or less.

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35. (Amended) A method of forming a Si nitride film as claimed in claim 33, wherein said nitriding step is conducted at a temperature of about 400°C.

37. (Amended) A method of forming an oxide film on a polysilicon pattern, characterized by the steps of:

forming a polysilicon pattern on an insulation film; and
oxidizing a surface and a sidewall of said polysilicon pattern to form an oxide film such that said oxide film covers said surface and said sidewall of said polysilicon pattern continuously,

said step of forming said oxide film comprising the steps of:

forming plasma by exciting an inert gas predominantly of Kr and an oxygen gas by a microwave; and

oxidizing a surface of said polysilicon pattern by atomic state oxygen O* formed with excitation of said plasma.

38. (Amended) A method of forming a nitride film on a polysilicon pattern, characterized by the steps of:

forming a polysilicon pattern on an insulation film; and
forming a nitride film by nitriding a surface and sidewall of said polysilicon pattern such that said nitride film covers said surface and said sidewall of said polysilicon pattern continuously;

said step of forming said nitride film comprising the steps of:

forming plasma by exciting an inert gas predominantly of Ar or Kr and a gas containing nitrogen as a constituent element by a microwave; and

nitriding a surface of said polysilicon pattern by hydrogen nitride radicals NH* formed with excitation of said plasma.

See the attached Appendix for the changes made to effect the above claim(s)